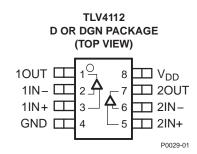




HIGH-OUTPUT-DRIVE OPERATIONAL AMPLIFIERS WITH SHUTDOWN

FEATURES

- Controlled Baseline
 - One Assembly Site
 - One Test Site
 - One Fabrication Site
- Extended Temperature Performance of -55°C to 125°C
- Enhanced Diminishing Manufacturing Sources (DMS) Support
- Enhanced Product-Change Notification
- Qualification Pedigree (1)
- High Output Drive . . . >300 mA
- Rail-To-Rail Output
- Unity-Gain Bandwidth . . . 2.7 MHz
- Slew Rate . . . 1.5 V/μs
- Supply Current . . . 700 μA/Per Channel
- Supply Voltage Range . . . 2.5 V to 6 V
- Universal Op Amp EVM
- (1) Component qualification in accordance with JEDEC and industry standards to ensure reliable operation over an extended temperature range. This includes, but is not limited to, Highly Accelerated Stress Test (HAST) or biased 85/85, temperature cycle, autoclave or unbiased HAST, electromigration, bond intermetallic life, and mold compound life. Such qualification testing should not be viewed as justifying use of this component beyond specified performance and environmental limits.



DESCRIPTION

The TLV411x single-supply operational amplifiers provide output currents in excess of 300 mA at 5 V. This enables standard pin-out amplifiers to be used as high current buffers or in coil driver applications. The TLV4110 and TLV4113 come with a shutdown feature.

The TLV411x is available in the ultra-small MSOP PowerPAD™ package, which offers the exceptional thermal impedance required for amplifiers delivering high current levels.

All TLV411x devices are offered in SOIC (single and dual) and MSOP PowerPAD (dual).

FAMILY PACKAGE TABLE

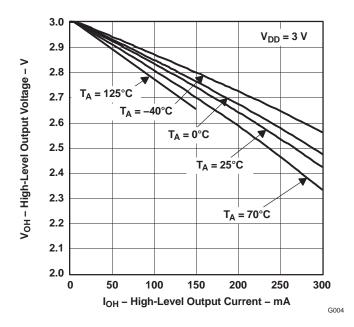
DEVICE	NUMBER OF	PACKAG	E TYPES	SHUTDOWN	UNIVERSAL EVM BOARD
DEVICE	CHANNELS	MSOP	SOIC	SHUIDOWN	UNIVERSAL EVM BOARD
TLV4110	1	8	8	Yes	
TLV4111	1	8	8	_	See the EVM Selection Cuide (SLOUGE)
TLV4112	2	8	8	_	See the EVM Selection Guide (SLOU060)
TLV4113	2	10	14	Yes	

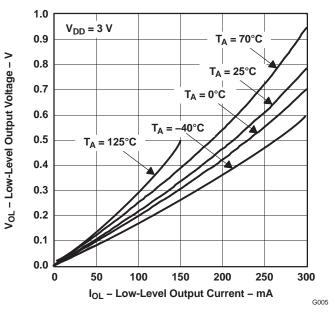


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PowerPAD is a trademark of Texas Instruments. Parts, Microsim PSpice are trademarks of MicroSim Corporation.







TLV4110 AND TLV4111 AVAILABLE OPTIONS

T _A	PACKAGED DEVICES								
		MSOP							
	SMALL OUTLINE (D) ^{(1) (2)}	SMALL OUTLINE (DGN) ⁽¹⁾	SYMBOL						
FEOC to 10FOC	TLV4110MDREP (3)	TLV4110MDGNREP ⁽³⁾	BTB						
–55°C to 125°C	TLV4111MDREP ⁽³⁾	TLV4111MDGNREP ⁽³⁾	BTC						

- (1) The R designation indicates package is taped and reeled.
- (2) In the SOIC package, the maximum RMS output power is thermally limited to 350 mW; 700 mW peaks can be driven, as long as the RMS value is less than 350 mW.
- (3) Product preview.

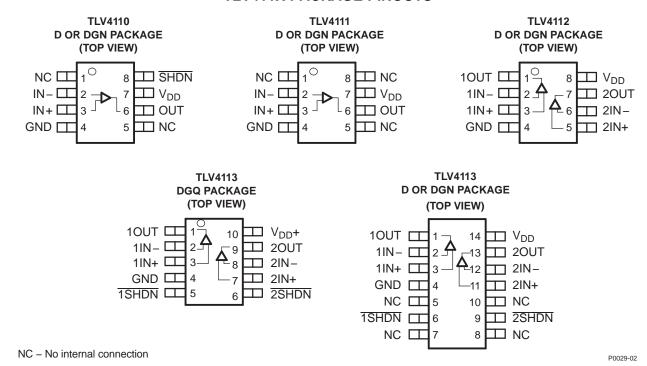
TLV4112 AND TLV4113 AVAILABLE OPTIONS

		PACKAGED DEVICES									
T _A	SMALL OUTLINE		MSOP								
• А	(D) (1) (2)	SMALL OUTLINE (DGN) ⁽¹⁾	SYMBOL	SMALL OUTLINE (DGQ) ⁽¹⁾	SYMBOL						
FF°C to 125°C	TLV4112MDREP (3)	TLV4112MDGNREP ⁽³⁾	BTD	-	_						
–55°C to 125°C	TLV4113MDREP ⁽³⁾	_	-	TLV4113MDGQREP	BTE						

- (1) The R designation indicates package is taped and reeled.
- (2) In the SOIC package, the maximum RMS output power is thermally limited to 350 mW; 700 mW peaks can be driven, as long as the RMS value is less than 350 mW.
- (3) Product preview.



TLV411X PACKAGE PINOUTS



ABSOLUTE MAXIMUM RATINGS

over operating free-air temperature range (unless otherwise noted)(1)

V_{DD}	Supply voltage ⁽²⁾	Supply voltage ⁽²⁾				
V_{ID}	Differential input voltage	Differential input voltage				
VI	Input voltage range			±V _{DD}		
Io	Output current ⁽³⁾			800 mA		
	Continuous DMC output ourrent (cook outp	ut of amplifier)	T _J ≤ 105°C	350 mA		
IO	Continuous RMS output current (each outp	ut or ampliller)	T _J ≤ 150°C	110 mA		
	Peak output current (each output of	T _J ≤ 105°C		500 mA		
IO	amplifier	T _J ≤ 150°C		155 mA		
	Continuous total power dissipation			See Dissipation Rating Table		
T _A	Operating free-air temperature range			−55°C to 125°C		
TJ	Maximum junction temperature	150°C				
T _{stg}	Storage temperature range	−65°C to 150°C				
	Lead temperature 1,6 mm (1/16 inch) from	case for 10 sec	conds	260°C		

⁽¹⁾ Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

⁽²⁾ All voltage values, except differential voltages, are with respect to GND.

⁽³⁾ To prevent permanent damage, the die temperature must not exceed the maximum junction temperature.

SGLS314D-JUNE 2006-REVISED MAY 2008

NSTRUMENTS

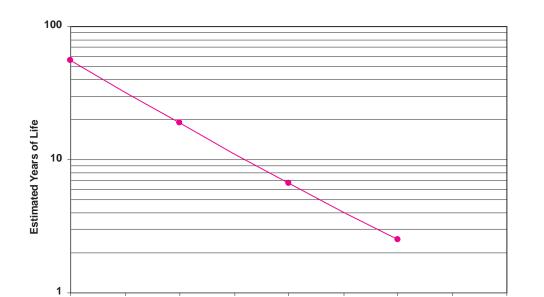


Figure 1. TLV4113MDGQ Wirebond Life

140

Continous $T_J - {}^{\circ}C$

145

150

155

160

135

DISSIPATION RATING TABLE

120

125

130

PACKAGE	θ _{JC} (°C/W)	θ _{JA} (°C/W)	T _A ≤ 25°C POWER RATING	T _A = 25°C POWER RATING
D (8)	38.3	176	710 mW	142 mW
D (14)	26.9	122.3	1022 mW	204.4 mW
DGN (8) ⁽¹⁾	4.7	52.7	2.37 W	474.4 mW
DGQ (10) ⁽¹⁾	4.7	52.3	2.39 W	478 mW

⁽¹⁾ See the Texas Instruments document, *PowerPAD Thermally Enhanced Package Application Report* (SLMA002), for more information on the PowerPAD package. The thermal data was measured on a PCB layout, based on information in the section entitled *Texas Instruments Recommended Board for PowerPAD*, on page 33 of SLMA002.



RECOMMENDED OPERATING CONDITIONS

				MIN	MAX	UNIT
V_{DD}	Supply voltage			2.5	6	V
V_{ICR}	Common-mode input voltage range			0	V _{DD} – 1.5	V
T _A	Operating free-air temperature			-55	125	°C
)//)	V _{DD} = 3 V	2.1		V
	Chartelesses towns as /off and to as leasel(1)	V(on)	V _{DD} = 5 V	3.8		V
	Shutdown turnon/off voltage level (1)	\/(off)	V _{DD} = 3 V		0.9	V
		V(off)	V _{DD} = 5 V		1.65	V

⁽¹⁾ Relative to GND

ELECTRICAL CHARACTERISTICS

at recommended operating conditions, $V_{DD} = 3 \text{ V}$ and 5 V (unless otherwise noted)

	PARAMETER	TEST COM	TEST CONDITIONS			TYP	MAX	UNIT
DC PER	FORMANCE						,	
V	Input offset voltage	$V_{IC} = V_{DD}/2, V_O = V_D$	$V_{IC} = V_{DD}/2, V_{O} = V_{DD}/2, R_{L} = 100 \Omega,$			175	3500	μV
V_{IO}	input onset voltage	$R_S = 50 \Omega$		Full range			4000	μν
α VIO	Offset voltage drift			25°C		3		μV/°C
CMRR	Common made rejection ratio	$V_{DD} = 3 \text{ V}, R_{S} = 50 \Omega$	$V_{IC} = 0 \text{ to } 2 \text{ V}$	25°C		63		dB
CIVIKK	Common-mode rejection ratio	$V_{DD} = 5 \text{ V}, R_{S} = 50 \text{ C}$	$V_{IC} = 0 \text{ to } 4 \text{ V}$	25°C		68		uБ
			P. – 100 O	25°C	78	84		
۸	Large-signal differential voltage amplification	V _{DD} = 3 V	$R_L = 100 \Omega$	Full range	67			dB
			D 40 kO	25°C	85	100		
			$R_L = 10 \text{ k}\Omega$	Full range	75			
A_{VD}			P 100 O	25°C	88	94		
		V _{DD} = 5 V	$R_L = 100 \Omega$	Full range	75			
		$v_{DD} = 3 v$	D 40 kO	25°C	90	110		
			$R_L = 10 \text{ k}\Omega$	Full range	85			
INPUT C	CHARACTERISTICS							
	Input offeet ourrent			25°C		0.3	25	pА
I _{IO} Input offset current							1000	рA
	Input bigg ourront					0.3	50	
I _{IB}	Input bias current			Full range			2000	pA
ri(d)	Differential input resistance			25°C		1000		GΩ
CIC	Common-mode input capacitance	f = 100 Hz		25°C		5		pF

⁽¹⁾ Full range is -55°C to 125°C.



ELECTRICAL CHARACTERISTICS (continued)

at specified free-air temperature, $V_{DD} = 3 \text{ V}$ and 5 V (unless otherwise noted)

	PARAMETER	TEST COM	TEST CONDITIONS		MIN	TYP	MAX	UNIT	
OUTPU	JT CHARACTERISTICS	·							
			10 mA	25°C	2.7	2.97			
		$V_{DD} = 3 V$,	$I_{OH} = -10 \text{ mA}$	Full range	2.6			V	
		$V_{IC} = V_{DD}/2$	1 100 m A	25°C	2.6	2.73		V	
\/	High lovel output voltage		$I_{OH} = -100 \text{ mA}$	Full range	2.5				
V _{OH}	High-level output voltage		10 mA	25°C	4.7	4.96			
		$V_{DD} = 5 V$	$I_{OH} = -10 \text{ mA}$	Full range	4.6			V	
		$V_{IC} = V_{DD}/2$	1 100 m A	25°C	4.6	4.76		V	
			$I_{OH} = -100 \text{ mA}$	Full range	4.5				
	Low-level output voltage		I _{OL} = 10 mA	25°C		0.03	0.1		
\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \		$V_{DD} = 3 \text{ V and 5 V},$		Full range			0.2	V	
V _{OL}		$V_{IC} = V_{DD}/2$		25°C		0.33	0.4		
			IOL = 100 IIIA	Full range			0.55		
	Output current	Measured at 0.5 V	Measured at 0.5 V V _{DD} = 3 V			±220		mA	
Io	Output current	from rail	$V_{DD} = 5 V$	25°C		±320		IIIA	
	Short circuit output current	Sourcing		25°C		800		mA	
Ios	Short-circuit output current	Sinking		25 C		800		ША	
POWE	R SUPPLY	·							
	Supply current (per channel)	V - V /2		25°C		700	1000		
I _{DD}	Supply current (per channel)	$V_O = V_{DD}/2$		Full range			1500	μA	
		$V_{DD} = 2.7 \text{ to } 3.3 \text{ V, N}$	o load	25°C	69	82		dB	
PSRR	Power supply rejection ratio	$V_{IC} = V_{DD}/2 V$		Full range	65			ub	
PORK	$(\Delta V_{DD} / \Delta V_{IO})$	$V_{DD} = 4.5 \text{ to } 5.5 \text{ V}, \text{ N}$	o load	25°C	69	79		dB	
		$V_{IC} = V_{DD}/2 V$		Full range	65			UD	

⁽¹⁾ Full range is -55°C to 125°C.



ELECTRICAL CHARACTERISTICS (continued)

at specified free-air temperature, $V_{DD} = 3 \text{ V}$ and 5 V (unless otherwise noted)

	PARAMETER	TEST CONDI	TIONS	T _A ⁽¹⁾	MIN	TYP	MAX	UNIT	
DYNAMIC	PERFORMANCE								
GBWP	Gain bandwidth product	$R_L = 100 \ \Omega, \ C_L = 10$	pF	25°C		2.7		MHz	
			V 2.V	25°C	0.8	1.57			
SR	Slew rate at unity gain	$V_{o(pp)} = 2.5 \text{ V},$ $R_L = 100 \Omega,$	$V_{DD} = 3 V$	Full range	0.4			V/µs	
SK	Siew rate at unity gain	$C_{L} = 100 \Omega,$ $C_{L} = 10 pF$	V _{DD} = 5 V	25°C	1	1.57		v/µS	
			$v_{DD} = 3 \text{ V}$	Full range	0.5				
φМ	Phase margin	$R_L = 100 \ \Omega, \ C_L = 10$	pF	25°C		66			
	Gain margin	$R_L = 100 \ \Omega, \ C_L = 10$	pF	25°C		16		dB	
		V(STEP) _{pp} = 1 V,	0.1%			0.7			
t _s	Settling time	$A_V = -1,$ $C_L = 10 \text{ pF},$ $R_L = 100 \Omega$	0.01%	25°C		1.3		μs	
NOISE/DIS	STORTION PERFORMANCE								
		$V_{O(nn)} = V_{DD}/2 V$	A _V = 1			0.025			
THD+N	Total harmonic distortion, plus noise	$V_{O(pp)} = V_{DD}/2 V$, $R_L = 100 \Omega$,	A _V = 10	25°C		0.035			
		f = 100 Hz	$A_{V} = 100$			0.15			
V _n	Equivalent input noise voltage	f = 100 Hz		25°C		55		nV/√ Hz	
v _n	Equivalent input noise voltage	f = 10 Hz		23 C		10		110/ 1112	
In	Equivalent input noise current	f = 1 Hz		25°C		0.31		fA/√ Hz	
SHUTDOV	WN CHARACTERISTICS								
1	Supply current in shutdown mode (per	SHDN = 0 V		25°C		3.4	10	μA	
I _{DD} (SHDN)	channel) (TLV4110, TLV4113)	SI IDIN = U V		Full range			15	μΑ	
t _(ON)	Amplifier turnon time (2)	R ₁ = 100 Ω		25°C		1			
t _(Off)	Amplifier turnoff time ⁽²⁾	V = 100 72		25 C		3.3		μs	

⁽¹⁾ Full range is -55°C to 125°C.

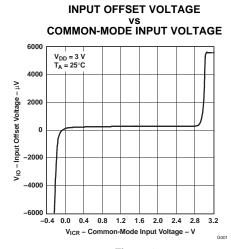
⁽²⁾ Disable time and enable time are defined as the interval between application of the logic signal to SHDN and the point at which the supply current has reached half its final value.

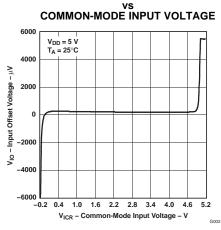


TYPICAL CHARACTERISTICS

Table of Graphs

			FIGURE
V _{IO}	Input offset voltage	vs Common-mode input voltage	2, 3
CMRR	Common-mode rejection ratio	vs Frequency	4
V _{OH}	High-level output voltage	vs High-level output current	5, 7
V _{OL}	Low-level output voltage	vs Low-level output current	6, 8
Z _o	Output impedance	vs Frequency	9
I _{DD}	Supply current	vs Supply voltage	10
k _{SVR}	Power supply voltage rejection ratio	vs Frequency	11
A _{VD}	Differential voltage amplification and phase	vs Frequency	12
	Gain-bandwidth product	vs Supply voltage	13
SR	Slew rate	vs Supply voltage	14
SK	Siew rate	vs Temperature	15
	Total harmonic distortion+noise	vs Frequency	16
V _n	Equivalent input voltage noise	vs Frequency	17
	Phase margin	vs Capacitive load	18
	Voltage-follower signal pulse response		19, 20
	Inverting large-signal pulse response		21
	Small-signal inverting pulse response		22
	Crosstalk	vs Frequency	23
	Shutdown forward and reverse isolation		24
	Shutdown supply current	vs Free-air temperature	25
	Shutdown supply current/output voltage		26





INPUT OFFSET VOLTAGE

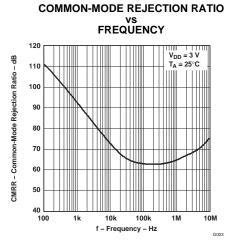
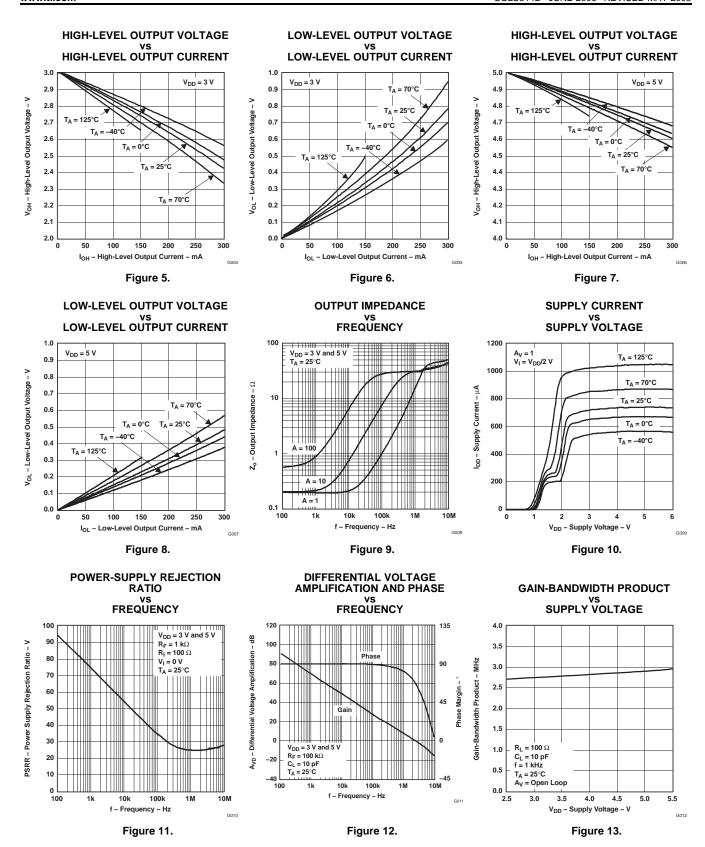


Figure 2.

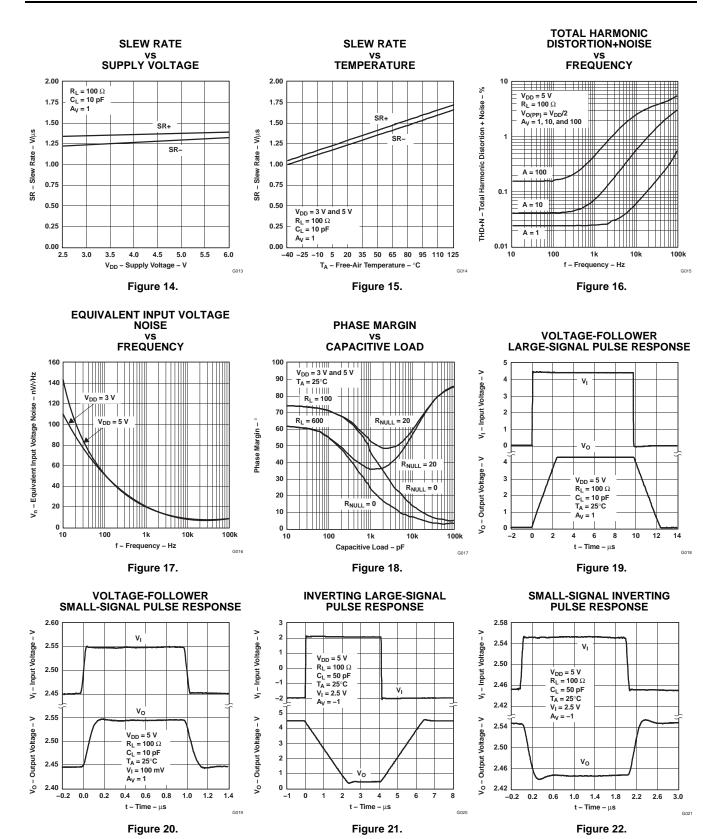
Figure 3.

Figure 4.

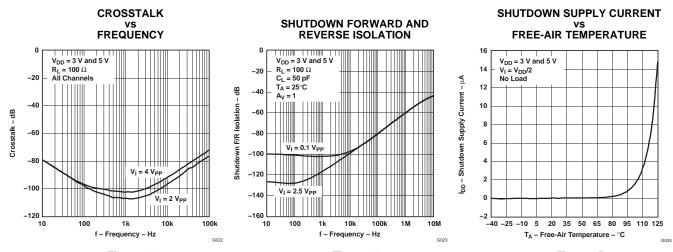


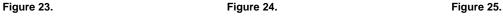












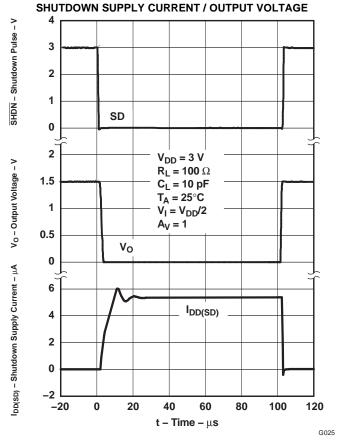


Figure 26.



APPLICATION INFORMATION

SHUTDOWN FUNCTION

Two members of the TLV411x family (TLV4110/3) have a shutdown terminal for conserving battery life in portable applications. When the shutdown terminal is tied low, the supply current is reduced to just nano amps per channel, the amplifier is disabled, and the outputs are placed in a high-impedance mode. In order to save power in shutdown mode, an external pullup resistor is required; therefore, to enable the amplifier, the shutdown terminal must be pulled high. When the shutdown terminal is left floating, care should be taken to ensure that parasitic leakage current at the shutdown terminal does not inadvertently place the operational amplifier into shutdown.

DRIVING A CAPACITIVE LOAD

When the amplifier is configured in this manner, capacitive loading directly on the output decreases the device's phase margin, leading to high-frequency ringing or oscillations. Therefore, for capacitive loads of greater than 1 nF, it is recommended that a resistor be placed in series \mathbb{R}_{NULL}) with the output of the amplifier, as shown in Figure 27. A maximum value of 20 Ω is recommended for most applications.

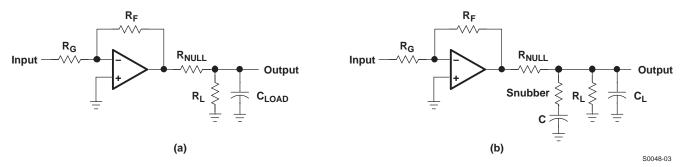


Figure 27. Driving a Capacitive Load

OFFSET VOLTAGE

The output offset voltage, (V_{OO}) is the sum of the input offset voltage (V_{IO}) and both input bias currents (I_{IB}) times the corresponding gains. The following schematic and formula can be used to calculate the output offset voltage.

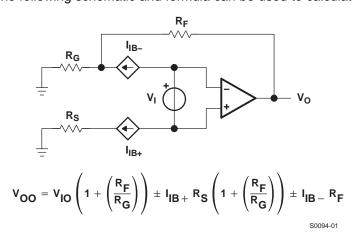


Figure 28. Output Offset Voltage Model



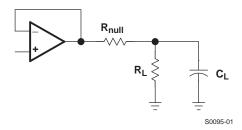


Figure 29.

GENERAL POWER DESIGN CONSIDERATIONS

When driving heavy loads at high junction temperatures there is an increased probability of electromigration affecting the long-term reliability of ICs. Therefore, to avoid this issue:

• The output current must be limited (at these high-junction temperatures).

OR

The junction temperature must be limited.

The maximum continuous output current at a die temperature 150°C will be 1/3 of the current at 105°C.

The junction temperature will be dependent on the ambient temperature around the IC, thermal impedance from the die to the ambient and power dissipated within the IC.

$$T_J = T_A + \theta_{JA} \times P_{DIS}$$

Where:

 P_{DIS} is the IC power dissipation and is equal to the output current multiplied by the voltage dropped across the output of the IC.

 θ_{IA} is the thermal impedance between the junction and the ambient temperature of the IC.

T_{.l} is the junction temperature.

 T_A is the ambient temperature.

Reducing one or more of these factors results in a reduced die temperature. The 8-pin SOIC (small outline integrated circuit) has a thermal impedance from junction to ambient of 176°C/W. For this reason it is recommended that the maximum power dissipation of the 8-pin SOIC package be limited to 350 mW, with peak dissipation of 700 mW as long as the RMS value is less than 350 mW.

The use of the MSOP PowerPAD™ dramatically reduces the thermal impedance from junction to case. And, with correct mounting, the reduced thermal impedance greatly increases the IC's permissible power dissipation and output current handling capability. For example, the power dissipation of the PowerPAD™ is increased to above 1 W. Sinusoidal and pulse-width modulated output signals also increase the output current capability. The equivalent dc current is proportional to the square-root of the duty cycle:

$$I_{DC(EQ)} = I_{Cont} \times \sqrt{\text{(duty cycle)}}$$
 (1)

CURRENT DUTY CYCLE AT PEAK RATED CURRENT	EQUIVALENT DC CURRENT AS A PERCENTAGE OF PEAK
100	100
70	84
50	71



Note that, with an operational amplifier, a duty cycle of 70% often results in the op-amp sourcing current 70% of the time and sinking current 30%; therefore, the equivalent dc current is still 0.84 times the continuous current rating at a particular junction temperature.

GENERAL PowerPAD DESIGN CONSIDERATIONS

The TLV411x is available in a thermally-enhanced PowerPAD family of packages. These packages are constructed using a downset lead frame upon which the die is mounted [see Figure 30(a) and Figure 30(b)]. This arrangement results in the lead frame being exposed as a thermal pad on the underside of the package [see Figure 30(c)]. Because this thermal pad has direct thermal contact with the die, excellent thermal performance can be achieved by providing a good thermal path away from the thermal pad.

The PowerPAD package allows for both assembly and thermal management in one manufacturing operation. During the surface-mount solder operation (when the leads are being soldered), the thermal pad can also be soldered to a copper area underneath the package. Through the use of thermal paths within this copper area, heat can be conducted away from the package into either a ground plane or other heat-dissipating device.

The PowerPAD package represents a breakthrough in combining the small area and ease of assembly of surface mount with the previously awkward mechanical methods of heat sinking.

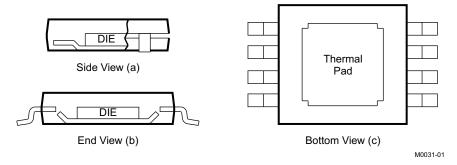


Figure 30. Views of Thermally Enhanced DGN Package



Although there are many ways to properly heatsink the PowerPAD package, the following steps illustrate the recommended approach.

- 1. Prepare the PCB with a top-side etch pattern, as shown in Figure 31. There should be etch for the leads as well as etch for the thermal pad.
- 2. Place five holes (dual) or nine holes (quad) in the area of the thermal pad. These holes should be 13 mils in diameter. Keep them small so that solder wicking through the holes is not a problem during reflow.
- 3. Additional vias may be placed anywhere along the thermal plane outside of the thermal pad area. This helps dissipate the heat generated by the TLV411x IC. These additional vias may be larger than the 13-mil diameter vias directly under the thermal pad. They can be larger because they are not in the thermal pad area to be soldered so that wicking is not a problem.
- 4. Connect all holes to the internal ground plane.
- 5. When connecting these holes to the ground plane, do not use the typical web or spoke via connection methodology. Web connections have a high thermal-resistance connection that is useful for slowing the heat transfer during soldering operations. This makes the soldering of vias that have plane connections easier. In this application, however, low thermal resistance is desired for the most efficient heat transfer. Therefore, the holes under the TLV411x PowerPAD package should make their connection to the internal ground plane with a complete connection around the entire circumference of the plated-through hole.
- 6. The top-side solder mask should leave the terminals of the package and the thermal pad area with its five holes (dual) or nine holes (quad) exposed. The bottom-side solder mask should cover the five or nine holes of the thermal pad area. This prevents solder from being pulled away from the thermal pad area during the reflow process.
- 7. Apply solder paste to the exposed thermal pad area and all of the IC terminals.
- 8. With these preparatory steps in place, the TLV411x IC is simply placed in position and run through the solder reflow operation as any standard surface-mount component. This results in a part that is properly installed.

Thermal Pad Area Single or Dual 68 mils × 70 mils) with 5 vias (Via diameter = 13 mils

Figure 31. PowerPAD PCB Etch and Via Pattern



For a given θ_{JA} , the maximum power dissipation is shown in Figure 32 and is calculated by the following formula:

$$P_{D} = \left(\frac{T_{MAX} - T_{A}}{\theta_{JA}}\right)$$

Where:

 P_D = Maximum power dissipation of TLV411x IC (watts)

 T_{MAX} = Absolute maximum junction temperature (150°C)

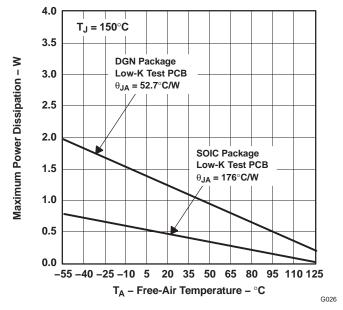
 T_A = Free-ambient air temperature (°C)

 $\theta_{JA} = \theta_{JC} + \theta_{CA}$

 θ_{JC} = Thermal coefficient from junction to case

 θ_{CA} = Thermal coefficient from case to ambient air (°C/W)

(2)



NOTE: Results are with no air flow and using JEDEC Standard Low-K test PCB.

Figure 32. Maximum Power Dissipation vs Free-Air Temperature

The next consideration is the package constraints. The two sources of heat within an amplifier are quiescent power and output power. The designer should never forget about the quiescent heat generated within the device, especially multi-amplifier devices. Because these devices have linear output stages (Class A-B), most of the heat dissipation is at low output voltages with high output currents.

The other key factor when dealing with power dissipation is how the devices are mounted on the PCB. The PowerPAD devices are extremely useful for heat dissipation. But, the device should always be soldered to a copper plane to fully use the heat dissipation properties of the PowerPAD. The SOIC package, on the other hand, is highly dependent on how it is mounted on the PCB. As more trace and copper area is placed around the device, θ_{JA} decreases and the heat-dissipation capability increases. The currents and voltages shown in these graphs are for the total package. For the dual or quad amplifier packages, the sum of the RMS output currents and voltages should be used to choose the proper package.



MACROMODEL INFORMATION

Macromodel information provided was derived using Microsim PartsTM, the model generation software used with Microsim PSpiceTM The Boyle macromodel (see Note 3) and subcircuit in Figure 33 are generated using the TLV411x typical electrical and operating characteristics at $T_A = 25^{\circ}C$. Using this information, output simulations of the following key parameters can be generated to a tolerance of 20% (in most cases).

- Maximum positive output voltage swing
- Maximum negative output voltage swing
- Slew rate
- Quiescent power dissipation
- · Input bias current
- Open-loop voltage amplification
- Unity-gain frequency

- Common-mode rejection ratio
- Phase margin
- DC output resistance
- AC output resistance
- Short-circuit output current limit

NOTE 3: G.R. Boyle, B. M. Cohn, D. O. Pederson, and J. E. Solomon, "Macromodeling of Integrated Circuit Operational Amplifiers," IEEE Journal of Solid-State Circuits, SC-9, 353 (1974).

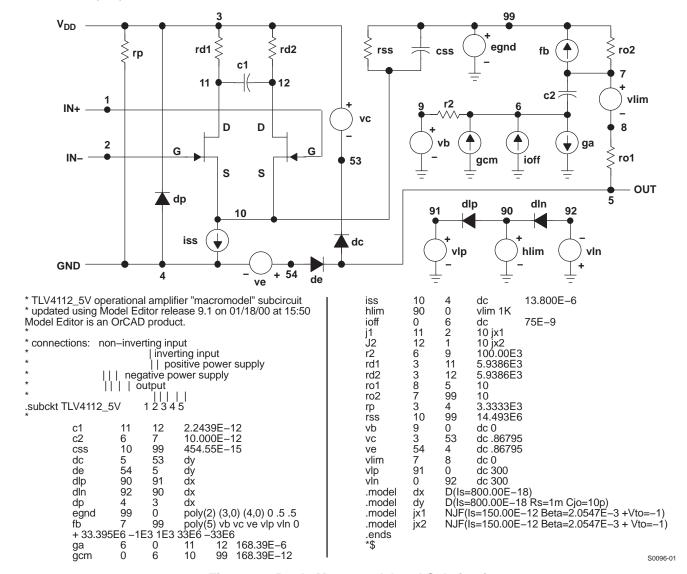


Figure 33. Boyle Macromodel and Subcircuit

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PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan ⁽²⁾	Lead/ Ball Finish	MSL Peak Temp ⁽³⁾	Samples (Requires Login)
TLV4113MDGQREP	ACTIVE	MSOP- PowerPAD	DGQ	10	2500	Green (RoHS & no Sb/Br)	CU NIPDAUAGI	Level-1-260C-UNLIM	
V62/06646-04ZE	ACTIVE	MSOP- PowerPAD	DGQ	10	2500	Green (RoHS & no Sb/Br)	CU NIPDAUAGI	evel-1-260C-UNLIM	

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

(3) MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

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OTHER QUALIFIED VERSIONS OF TLV4113-EP:

Catalog: TLV4113

NOTE: Qualified Version Definitions:



23-Jan-2012

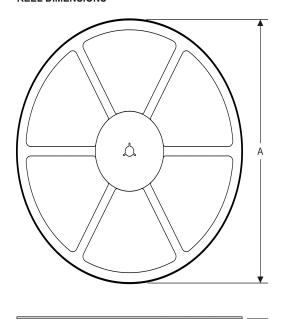
Catalog - TI's standard catalog product

PACKAGE MATERIALS INFORMATION

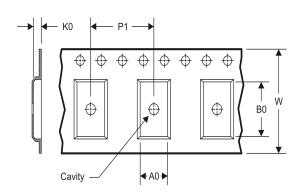
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TAPE AND REEL INFORMATION

REEL DIMENSIONS



TAPE DIMENSIONS



A0	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

TAPE AND REEL INFORMATION

*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TLV4113MDGQREP	MSOP- Power PAD	DGQ	10	2500	330.0	12.4	5.3	3.4	1.4	8.0	12.0	Q1

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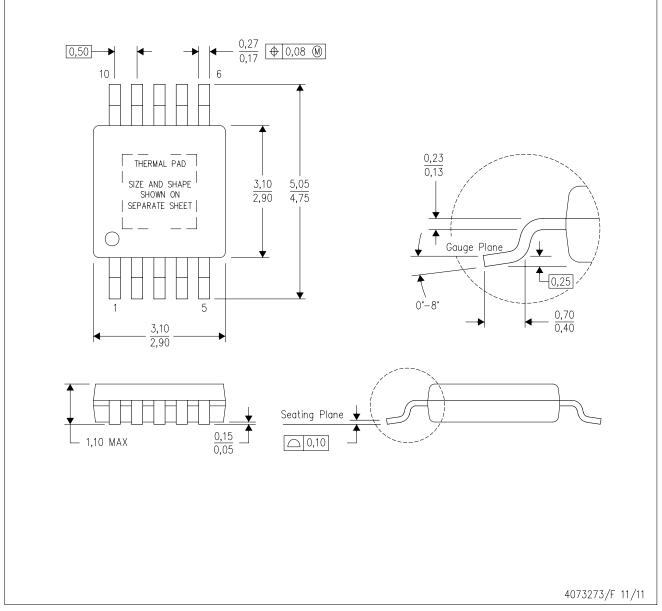


*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TLV4113MDGQREP	MSOP-PowerPAD	DGQ	10	2500	358.0	335.0	35.0

DGQ (S-PDSO-G10)

PowerPAD™ PLASTIC SMALL OUTLINE



NOTES:

- All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion not to exceed 0,15.
- D. This package is designed to be soldered to a thermal pad on the board. Refer to Technical Brief, PowerPad Thermally Enhanced Package, Texas Instruments Literature No. SLMA002 for information regarding recommended board layout. This document is available at www.ti.com http://www.ti.com>.
- E. See the additional figure in the Product Data Sheet for details regarding the exposed thermal pad features and dimensions. F. Falls within JEDEC MO-187 variation BA-T.

PowerPAD is a trademark of Texas Instruments.



DGQ (S-PDSO-G10)

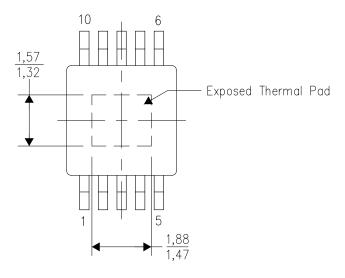
PowerPAD™ PLASTIC SMALL OUTLINE

THERMAL INFORMATION

This PowerPAD $^{\text{TM}}$ package incorporates an exposed thermal pad that is designed to be attached to a printed circuit board (PCB). The thermal pad must be soldered directly to the PCB. After soldering, the PCB can be used as a heatsink. In addition, through the use of thermal vias, the thermal pad can be attached directly to the appropriate copper plane shown in the electrical schematic for the device, or alternatively, can be attached to a special heatsink structure designed into the PCB. This design optimizes the heat transfer from the integrated circuit (IC).

For additional information on the PowerPAD package and how to take advantage of its heat dissipating abilities, refer to Technical Brief, PowerPAD Thermally Enhanced Package, Texas Instruments Literature No. SLMA002 and Application Brief, PowerPAD Made Easy, Texas Instruments Literature No. SLMA004. Both documents are available at www.ti.com.

The exposed thermal pad dimensions for this package are shown in the following illustration.



Top View

Exposed Thermal Pad Dimensions

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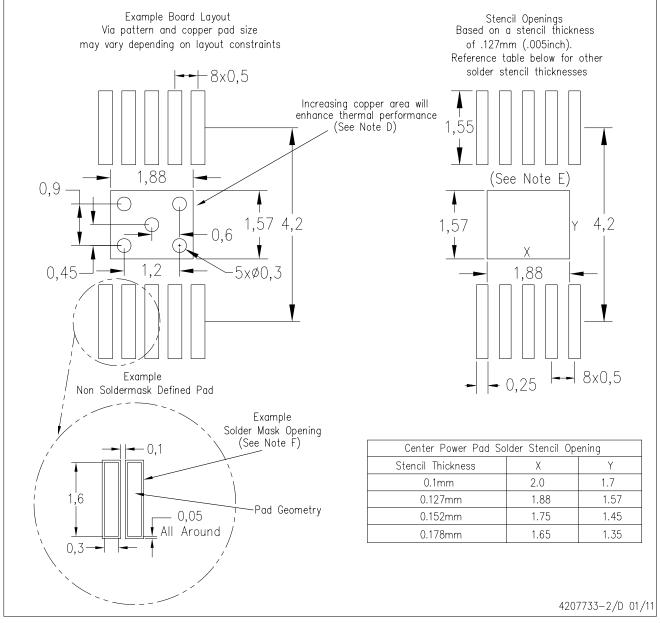
NOTE: A. All linear dimensions are in millimeters

PowerPAD is a trademark of Texas Instruments



DGQ (S-PDSO-G10)

PowerPAD™ PLASTIC SMALL OUTLINE



NOTES:

- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Customers should place a note on the circuit board fabrication drawing not to alter the center solder mask defined pad.
- D. This package is designed to be soldered to a thermal pad on the board. Refer to Technical Brief, PowerPad Thermally Enhanced Package, Texas Instruments Literature No. SLMA002, SLMA004, and also the Product Data Sheets for specific thermal information, via requirements, and recommended board layout. These documents are available at www.ti.com http://www.ti.com. Publication IPC-7351 is recommended for alternate designs.
- E. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Example stencil design based on a 50% volumetric metal load solder paste. Refer to IPC-7525 for other stencil recommendations.
- F. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.

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